

0.5-V Highly Power-Efficient Programmable Logic using Nonvolatile Configuration Switch in BEOL

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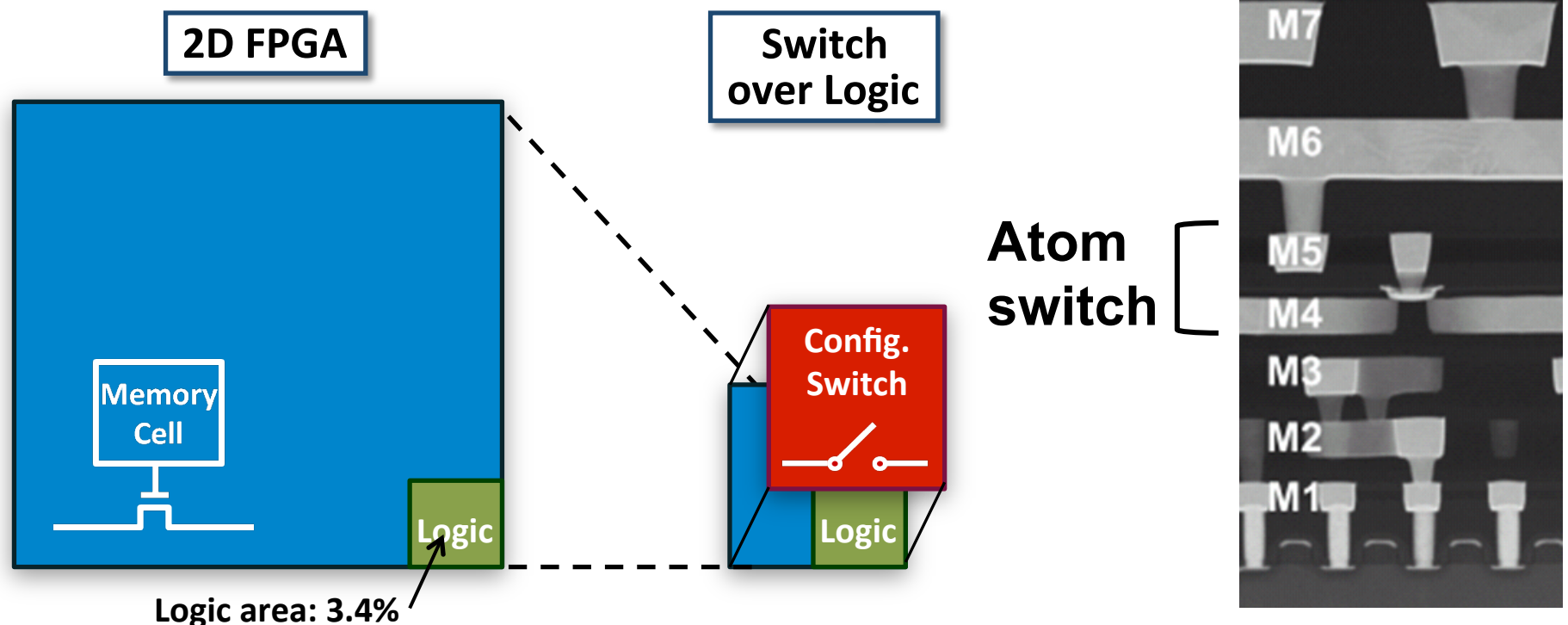
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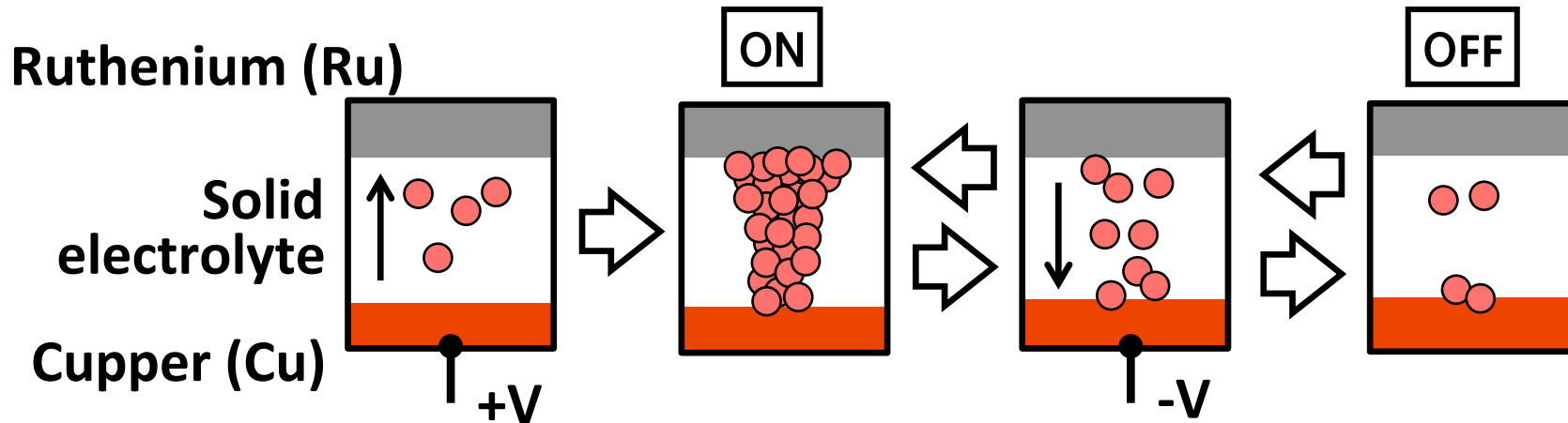
Concept of “Switch Over Logic”

- Nonvolatile switch is stacked on logic plane
 - Reduced cell area (Stacked switch plane)
 - Low Power (Nonvolatility / Shorter wiring length)
 - Complementary Atom SW reduces programming voltage



Operation principle

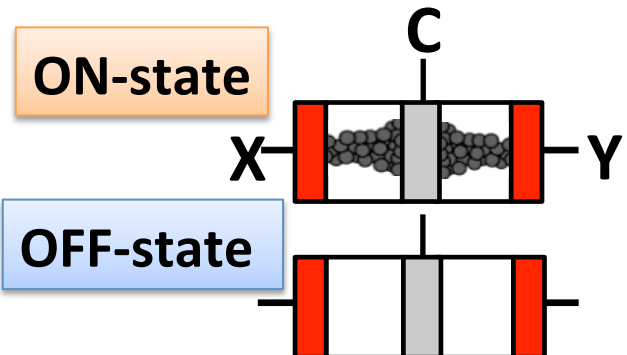
- Atom switch : Nanometer-scale Cu bridge forms between two electrodes via electrochemical reaction.



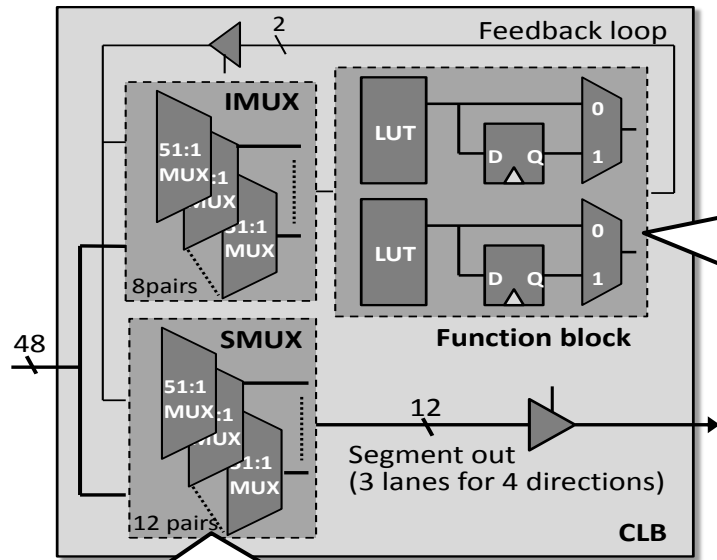
□ Features

- Nonvolatile
- Small input capacitance (1/10 of CMOS)
- Rewritable ($>10^3$)
- BEOL integration (small area)

Complementary Atom Switch (CAS)

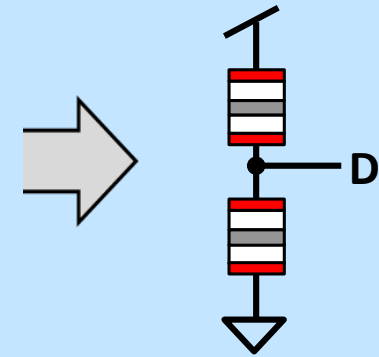
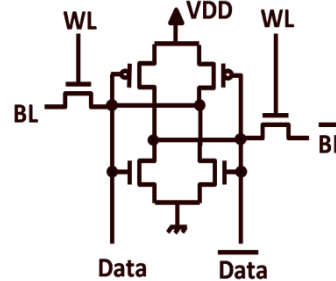


CAS-based Configurable Logic Block



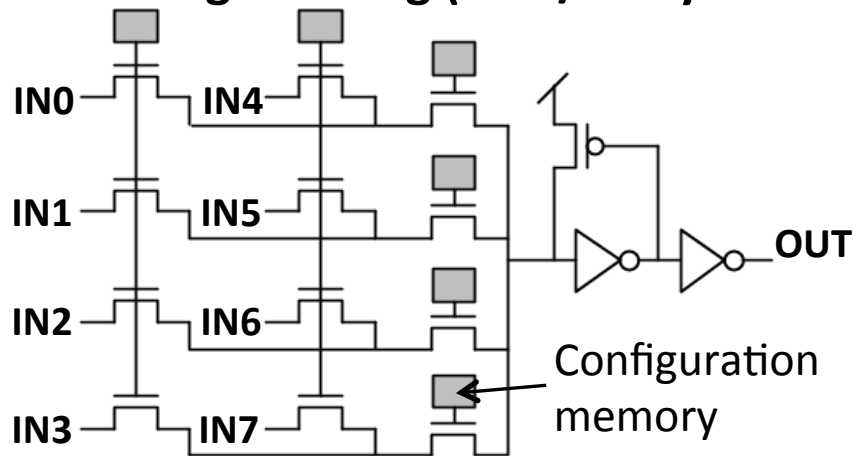
CAS-based memories - Nonvolatile

Conventional SRAM



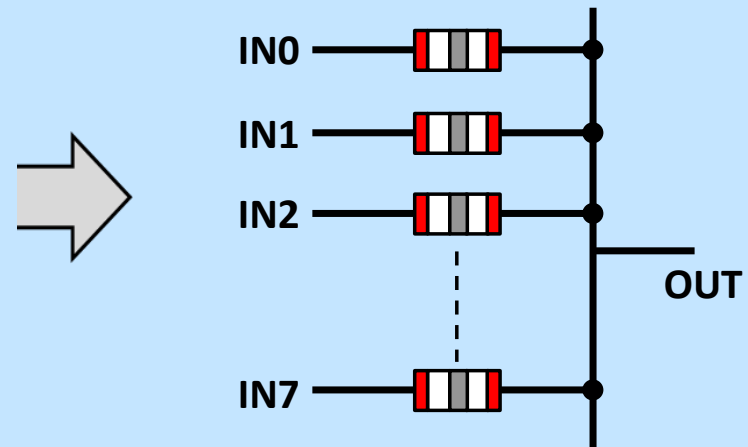
Conventional MUX

- Multi-stage routing (area/delay tradeoff)



CAS-based MUX

- Single-stage routing
- Small C_{in} (0.14fF/CAS)

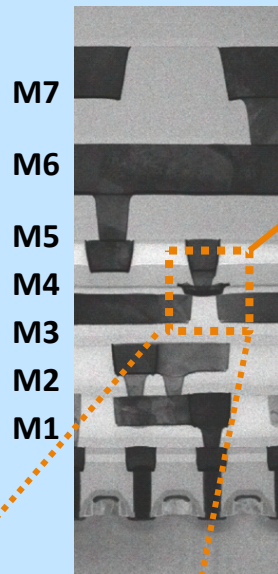


Physical implementation

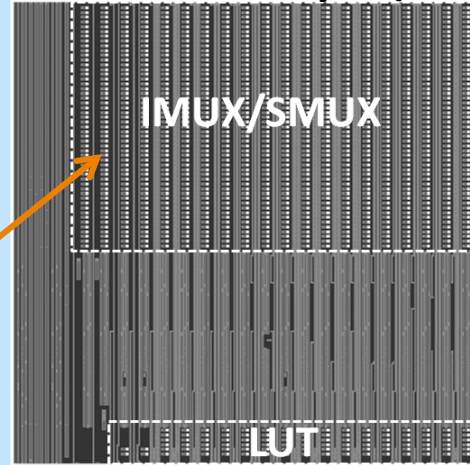
□ CASs are embedded in M4-M5 with 65nm-node CMOS process.

- 2 additional masks for CAS
- M1-5 local metal
- M6-7 semi-global metal

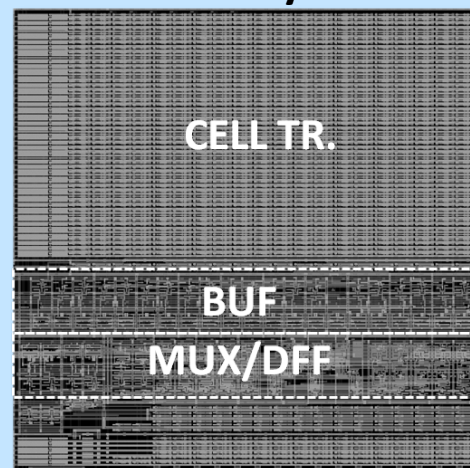
Cross-sectional TEM view



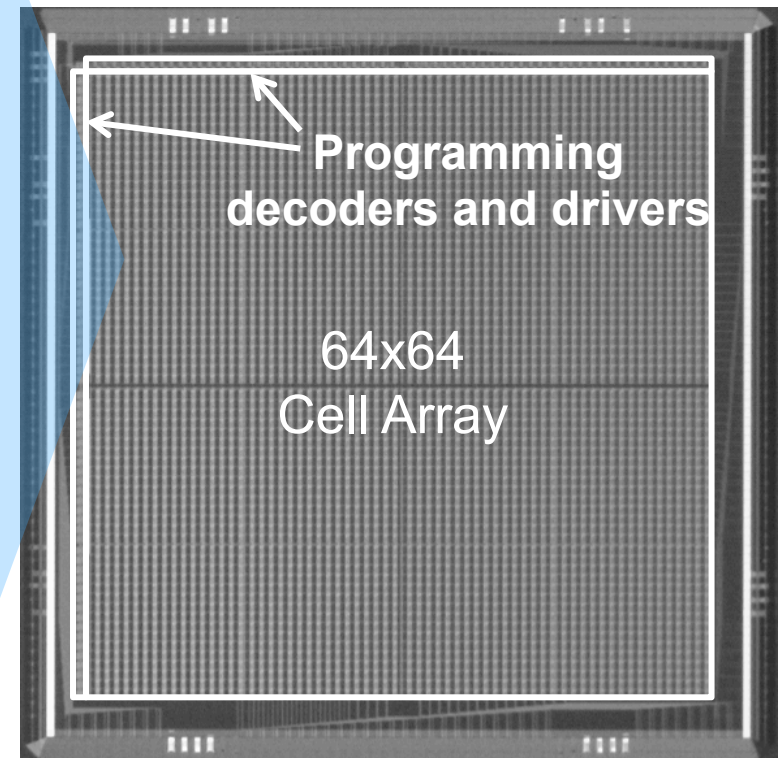
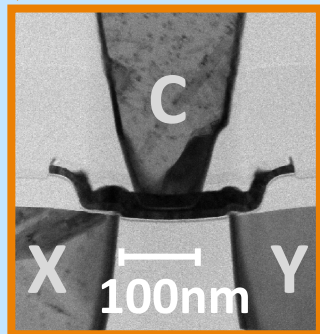
Interconnect layer (BEOL)



Transistor Layer



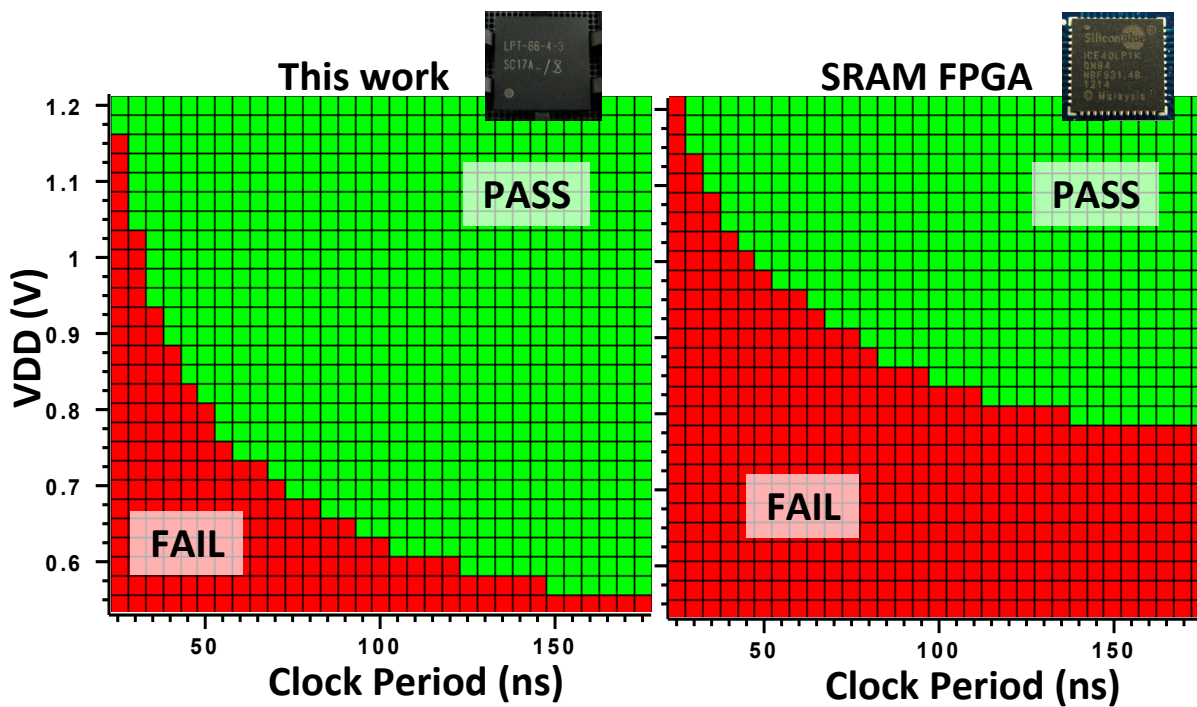
CAS



4.6M-bit CAS integrated

Low power/high performance of AtomSW-FPGA

- Comparison with commercial low-power FPGA
 - 64x64 AtomSW-FPGA vs SRAM-based FPGA
 - 16b-ALU/Signal-generator are mapped using 332 LUTs.
 - Dynamic power : -30% at minimum operating voltage
 - Critical path delay : -60% for VDD=0.8V



	AtomSW FPGA	SRAM FPGA*
Routing SW	AtomSW	SRAM, Pass Tr.
Process node	65nm	40nm
# of LUTs	8192	1280
Max. speed @0.8V	18.2MHz	7.1MHz
VDDmin @15MHz	0.73V	0.94V
Dynamic power @ VDDmin	28.0 μ W/ MHz	39.5 μ W/ MHz
Active power @ VDDmin	550 μ W	630 μ W

*<http://www.latticesemi.com/Products/FPGAandCPLD/iCE40.aspx>

Acknowledgements

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